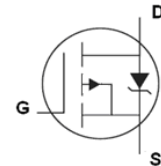


## Features

- P-Channel
- Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=-4.5\text{ V}$
- Fast Switching
- High conversion efficiency
- Pb-free lead plating; RoHS compliant

$V_{DS}$	-30	V
$R_{DS(on),TYP}$ @ $V_{GS}=-10\text{ V}$	23	m $\Omega$
$R_{DS(on),TYP}$ @ $V_{GS}=-4.5\text{ V}$	28	m $\Omega$
$I_D$	-8	A



Part ID	Package Type	Marking	Tape and reel information
VSO030P03LS	SOP8	030P03L	3000pcs/reel

Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (<math>T_c=25\text{ }^\circ\text{C}</math> Unless Otherwise Noted)</b>				
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30	V	
$T_j$	Maximum Junction Temperature	150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$	
$I_S$	Diode Continuous Forward Current	$T_c=25\text{ }^\circ\text{C}$ -8	A	
<b>Mounted on Large Heat Sink</b>				
$I_D$	Continuous Drain current @ $V_{GS}=-10\text{ V}$	$T_c=25\text{ }^\circ\text{C}$	-8	A
		$T_c=100\text{ }^\circ\text{C}$	-5	A
$I_{DM}$	Pulse Drain Current Tested ①	$T_c=25\text{ }^\circ\text{C}$	-32	A
$P_D$	Maximum Power Dissipation	$T_c=25\text{ }^\circ\text{C}$	2	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		62.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		50	$^\circ\text{C/W}$

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current(Tc=25°C)	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(Tc=125°C)	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	--	--	100	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.5	-1.0	-1.5	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>②</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-8A	--	23	30	mΩ
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>②</sup>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	--	28	35	mΩ
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>②</sup>	V <sub>GS</sub> =-4.2V, I <sub>D</sub> =-3A	--	30	40	mΩ
<b>Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	--	1080	--	pF
C <sub>oss</sub>	Output Capacitance		--	195	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	110	--	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4A, V <sub>GS</sub> =-4.5V	--	10.4	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	2.9	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	3.6	--	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =-15V, I <sub>D</sub> =-2A, R <sub>G</sub> =6.8Ω, V <sub>GS</sub> =-10V	--	11	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	7	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	22	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	7	--	nS
<b>Source- Drain Diode Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
I <sub>SD</sub>	Source-drain current(Body Diode)	T <sub>c</sub> =25°C	--	--	-8	A
V <sub>SD</sub>	Forward on voltage	I <sub>SD</sub> =-1A, V <sub>GS</sub> =0V	--	-0.74	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	T <sub>J</sub> =25°C, I <sub>sd</sub> =-8A, V <sub>GS</sub> =0V	--	21	--	nS
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=-100A/μs		12.5		nC

**NOTE:**

- ① Repetitive rating; pulse width limited by max. junction temperature.  
 ② Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

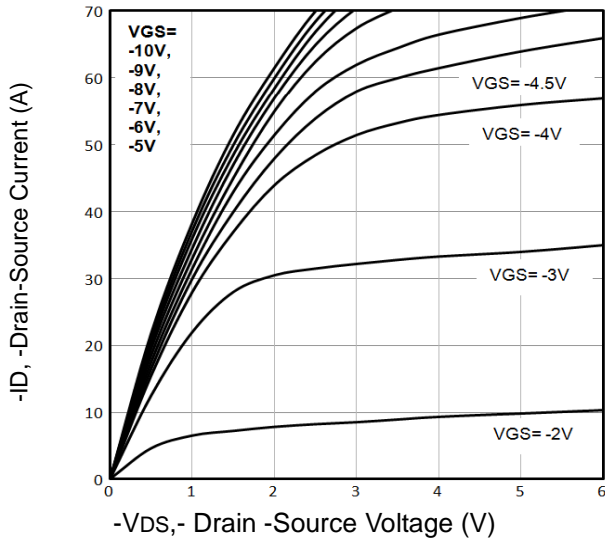


Fig1. Typical Output Characteristics

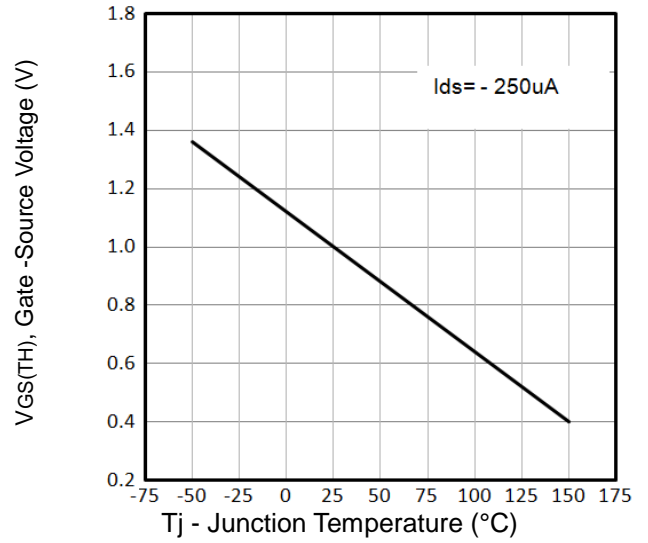


Fig2. Threshold Voltage Vs. Temperature

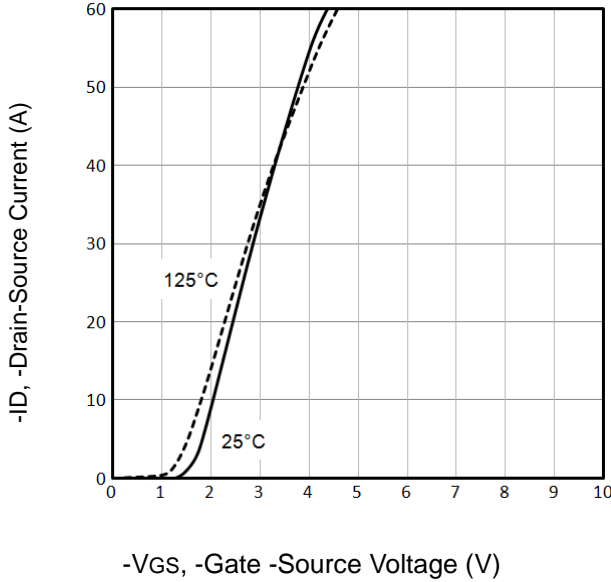


Fig3. Typical Transfer Characteristics

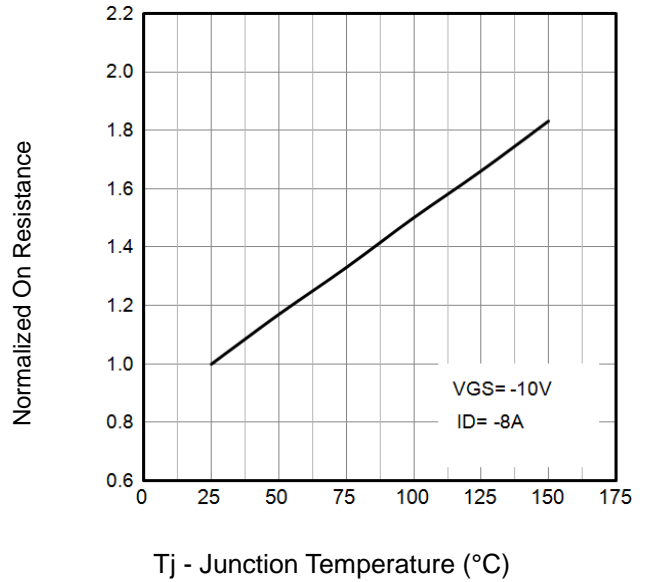


Fig4. Normalized On-Resistance Vs. Temperature

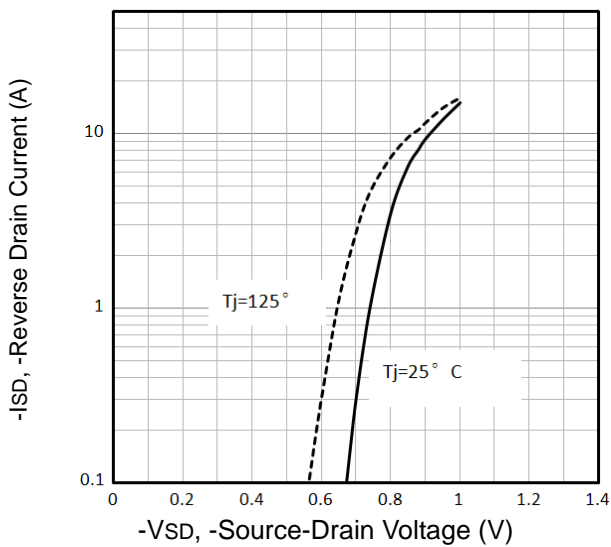


Fig5. Typical Source-Drain Diode Forward Voltage

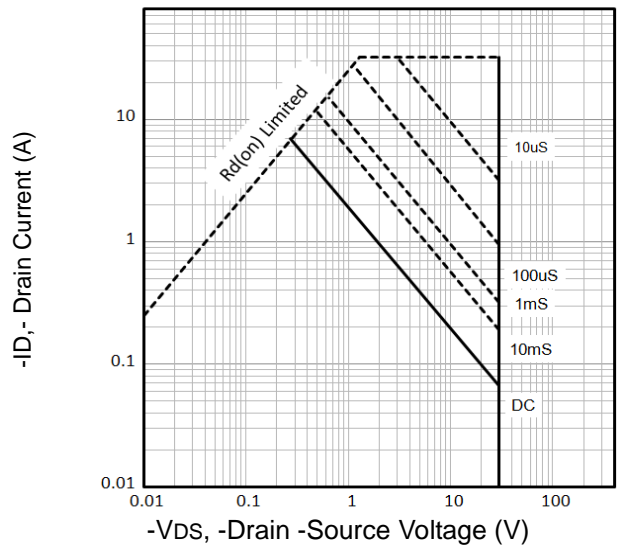


Fig6. Maximum Safe Operating Area

Typical Characteristics

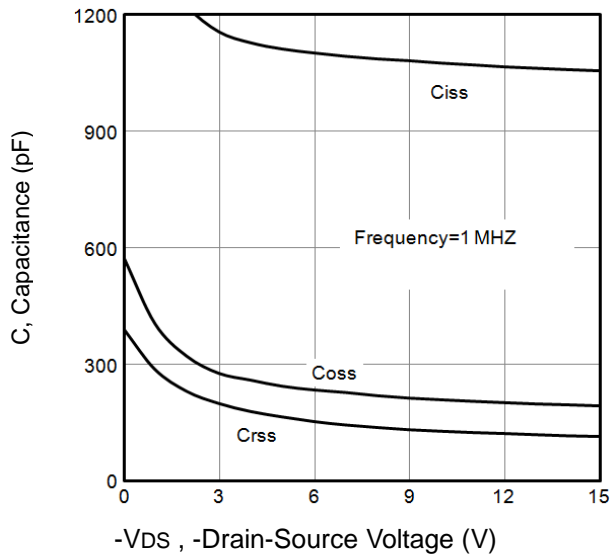


Fig7. Typical Capacitance Vs.Drain-Source Voltage

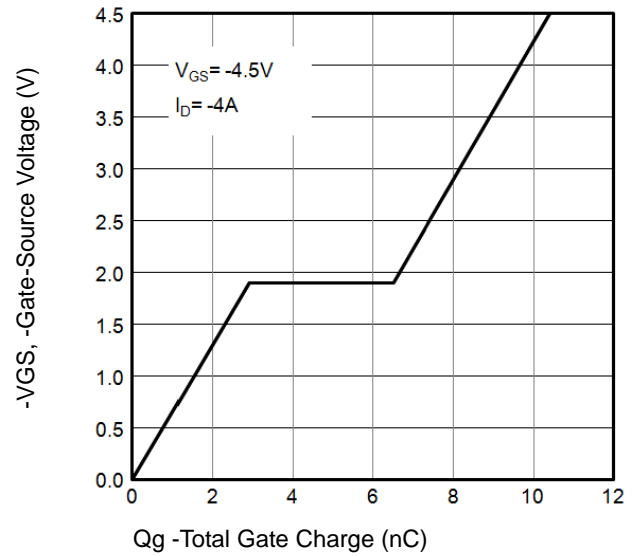


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

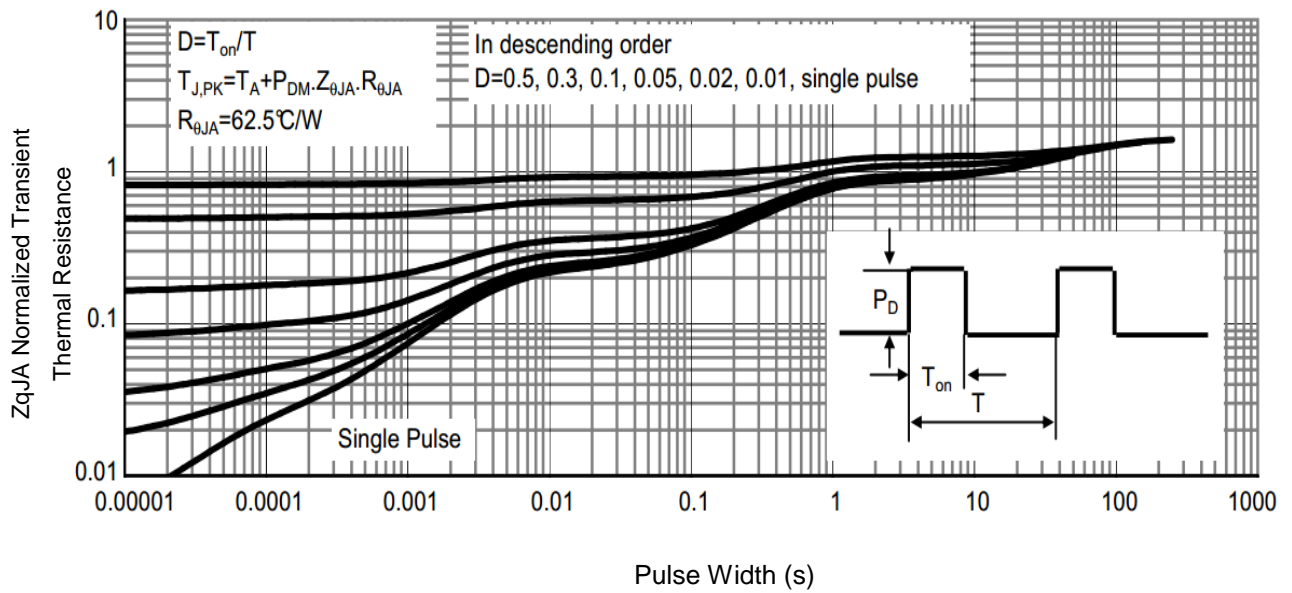


Fig9. Normalized Maximum Transient Thermal Impedance (Note F)

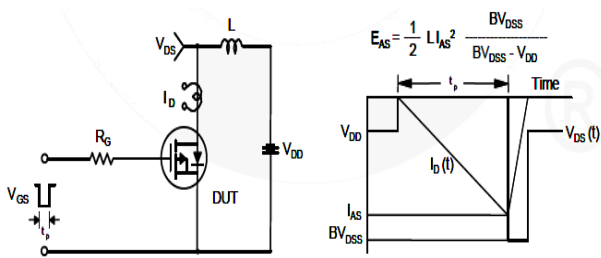


Fig10. Unclamped Inductive Test Circuit and Waveforms

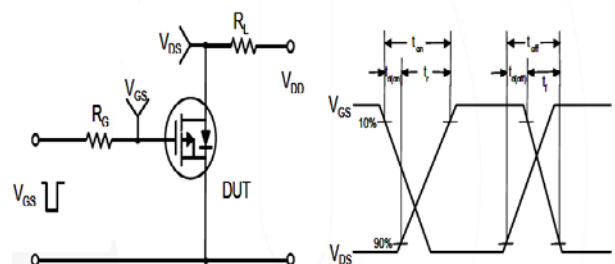
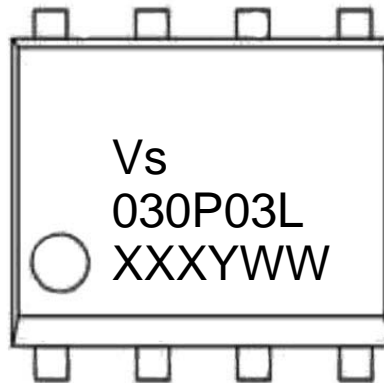


Fig11. Switching Time Test Circuit and waveforms

## Marking Information



1<sup>st</sup> line: Company Code (Vs), Company Logo

2<sup>nd</sup> line: Part Number (030P03L)

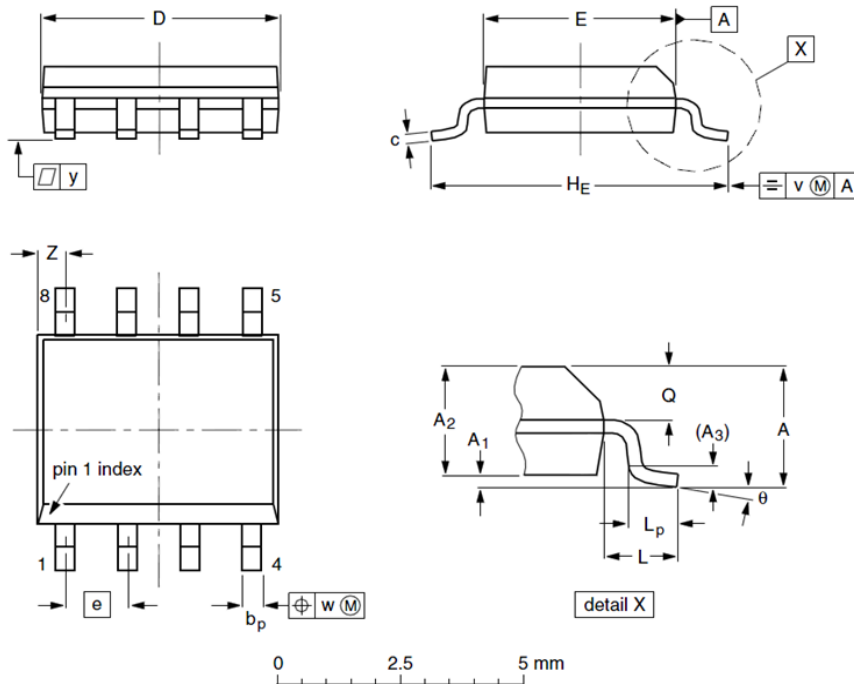
3<sup>rd</sup> line: Date code (XXXYWW)

XXX: Wafer Lot Number

Y: Year Code, e.g. E means 2017

WW: Week Code

### SOP8 Package Outline Data



Label	Dimensions (unit: mm)		
	Min	Typ	Max
A	--	--	1.75
A <sub>1</sub>	0.10	0.18	0.25
A <sub>2</sub>	1.25	1.35	1.50
A <sub>3</sub>	--	0.25	--
b <sub>p</sub>	0.36	0.42	0.51
c	0.19	0.22	0.25
D	4.80	4.92	5.00
E	3.80	3.90	4.00
e	--	1.27	--
H <sub>E</sub>	5.80	6.00	6.20
L	--	1.05	--
L <sub>p</sub>	0.40	0.68	1.00
Q	0.60	0.65	0.725
v	--	0.25	--
w	--	0.25	--
y	--	0.10	--
Z	0.30	0.50	0.70
θ	0°		8°

#### Notes:

1. Follow JEDEC MS-012.
2. Dimension "D" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15mm per side.
3. Dimension "E" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.25mm per side.
4. Dimension "bp" does NOT include dambar protrusion. Allowable dambar protrusion shall be 0.1mm total in excess of "bp" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot.

## Customer Service

#### Sales and Service:

[sales@vgsemi.com](mailto:sales@vgsemi.com)

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